

Comparison of the grain boundary chemistry of Ta and Ti doped high J_c Nb_3Sn strand by atomic resolution microscopy

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*The Applied Superconductivity Center
The National High Magnetic Field Laboratory
Florida State University*



Motivation

- Ta and Ti are widely used as dopants for Nb₃Sn superconducting strands to improve high field J_c and H_{c2} .
- Ti-doped Nb₃Sn high- J_c wires have shown better irreversible strand degradation than Ta-doped high J_c strand.
 - The mechanism is not known and cannot be explained by macrostructural features of the conductor architecture.
- GBs (grain boundaries) are believed vital both for high J_c and mechanical properties.
 - This work studies the GB segregation properties of Ta or Ti doped Nb₃Sn.



Methodology

- 4 different Nb₃Sn strands.
 - One ITER type Ti-doped Nb₃Sn strand and three high J_c (Ta, Ti, or Ta+Ti) doped RRP[®] Nb₃Sn strands
- μ -scale compositional analysis for A15 phase identification
 - EDS (Energy Dispersive X-ray spectroscopy) in FE-SEM
- nano-scale investigation of A15 GB properties
 - Good electron transparent TEM foil for high resolution electron microscopy
 - Atomic resolution TEM/STEM
 - EDS (Energy Dispersive X-ray Spectroscopy)
 - EFTEM (Energy Filtered transmission electron microscopy)
 - EELS (Energy Loss Spectroscopy)



Our capability for analytical microscopy

- JEOL-ARM 200cF (TEM/STEM) with BF, ADF, HAADF
- Spectroscopy: EDS and Dual EELS system
- Dual Beam FE-SEM/FIB system with GIS (Gas Injection System) + Nano-manipulator for TEM sample Prep.
- FE-SEM with EDS (SDD detector)

JEM-ARM 200cF



Carl Zeiss 1540 Esb: Dual Beam FE-SEM/FIB + GIS

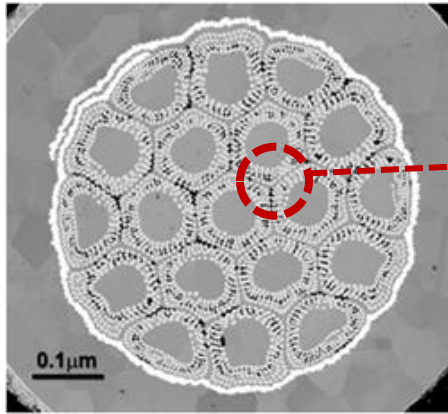


Omniprobe: Auto Probe 200.2

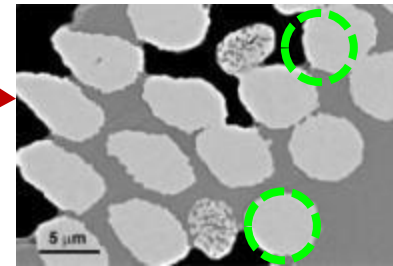
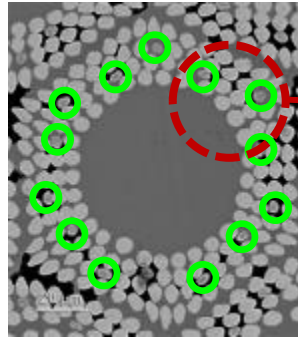


Description of samples

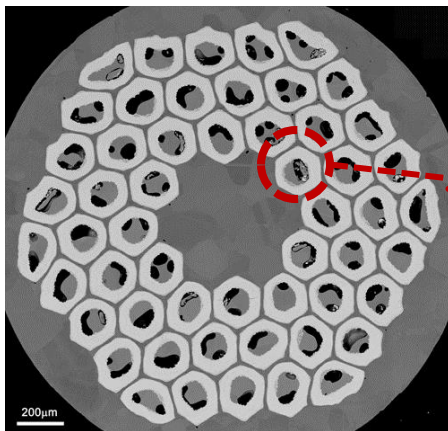
Sample type A: Ti-doped ITER Internal Sn strand, 650°C/200hrs



12 distributed Ti sources (Nb-47wt% Ti) in the sub element



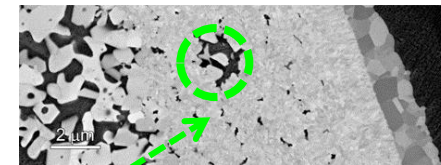
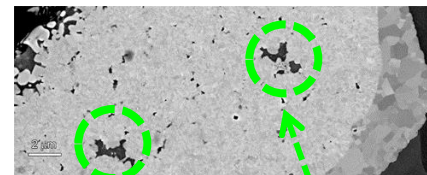
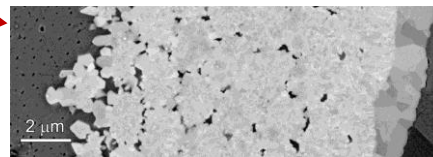
Sample type B: Ti or Ta-doped high J_c Internal Sn RRP® strands, 54/61, 640°C/48hrs



1. 7.5wt% Ta

2. 7.5wt% Ta + 0.3wt% Ti

3. 2at%Ti



Ti source



Irreversible strain results: Ti doping shows higher $\epsilon_{irr,0}$

Strand Type	Doping method	\varnothing (mm)	HT (°C/hrs)	$\epsilon_{irr,0}$ (%) Avg. 0.1 mV/cm	Non-Cu ac-loss (mJ/cm ³)
ITER	Dispersed Nb-Ti rods in pure Nb filaments	0.77	650/200	0.21	2136
RRP (54/61)	7.5wt% Ta in each filament	0.7	640/48	0.04	4815
RRP (54/61)	7.5wt% Ta + 0.3wt% Ti in each filament	0.7	640/48	0.06	4812
RRP (54/61)	2at% Ti in each filament	0.7	640/48	0.24	4670

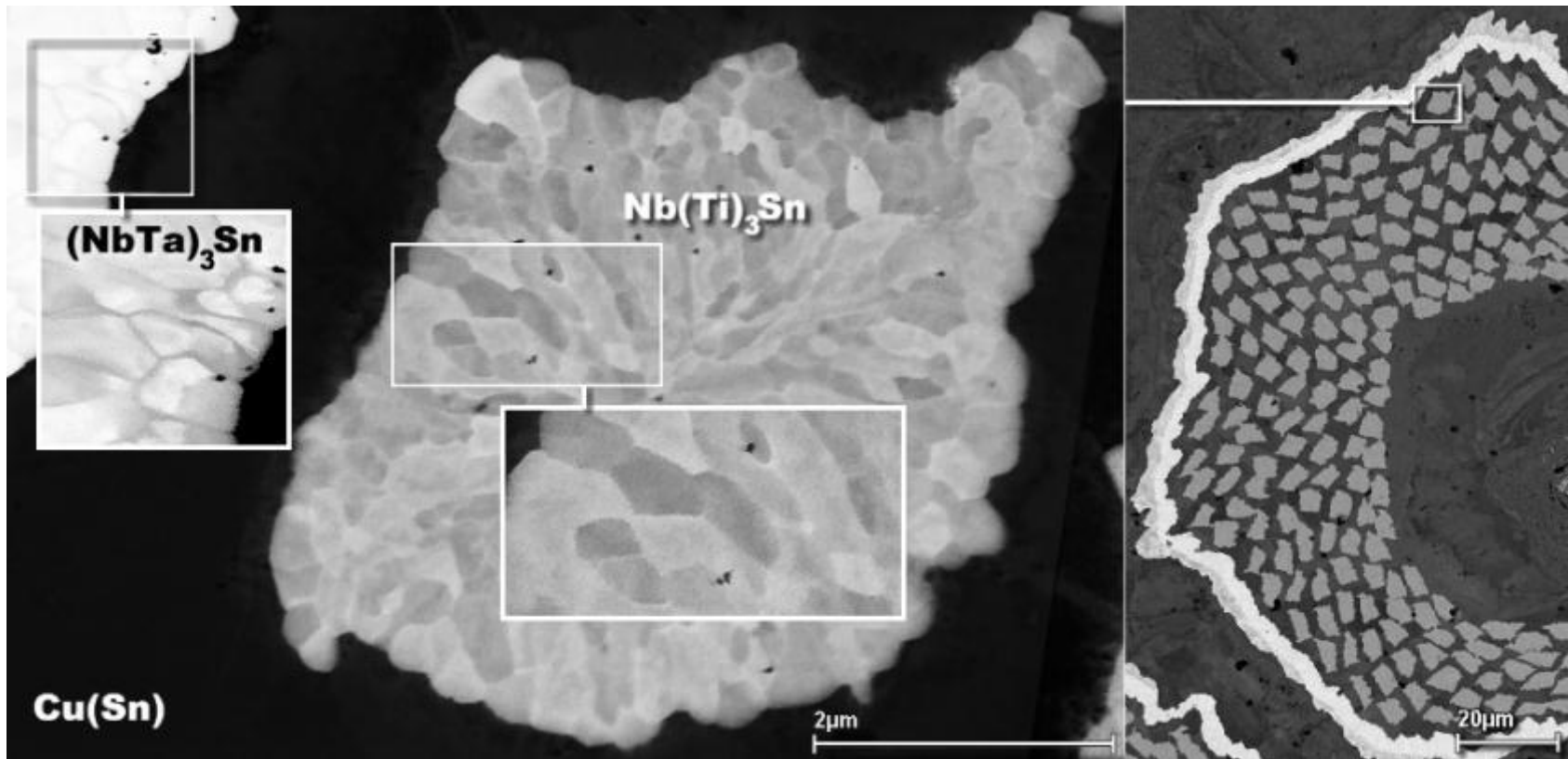
Measurement by Dr. N. Cheggour



Nb₃Sn: Grain boundary composition

GBs are known to be Sn-poor, the effect of Ti and Ta-doping on grain boundary composition needs to be determined.

Imaging by Dr. Peter Lee

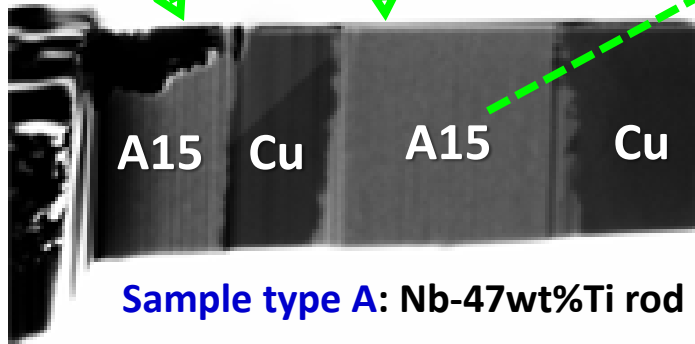
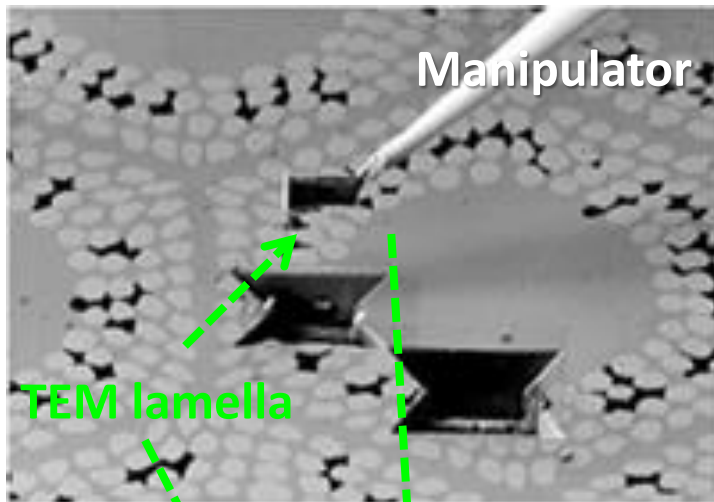


ITER-CSMC Benchmark III MJR internal Nb(Ti)₃Sn(Mg) strand cross-section: TWC (final HT 256hrs@750°C).

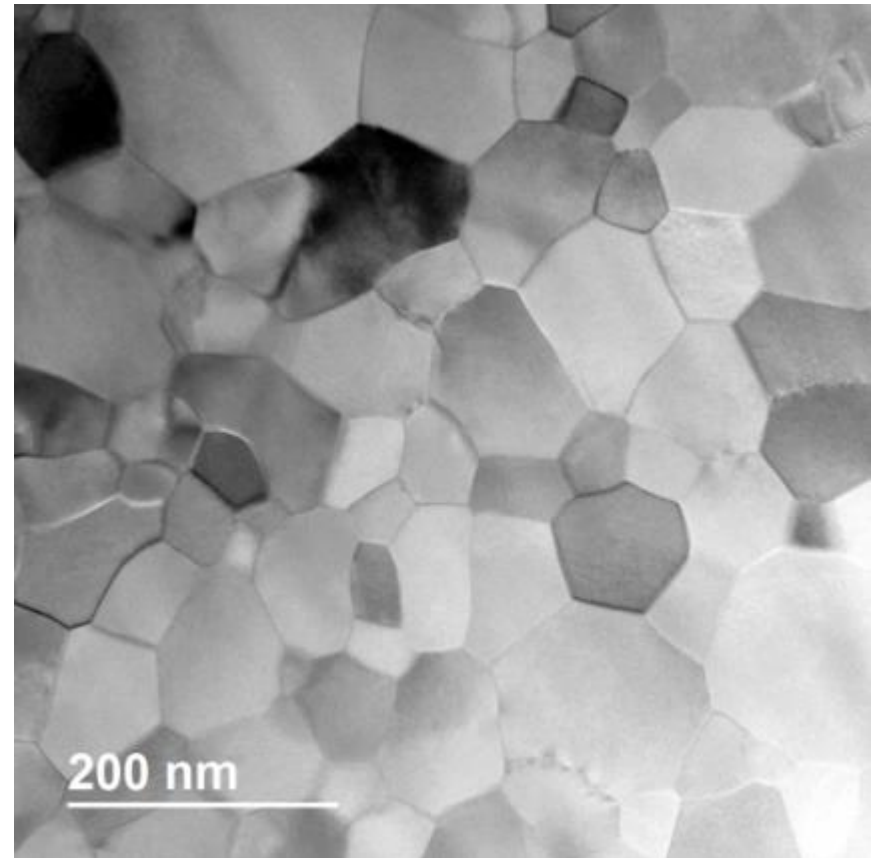


Atomic resolution analytical TEM/STEM can address: **Does the dopant segregate at GBs?**

TEM sampling by FIB + GIS system

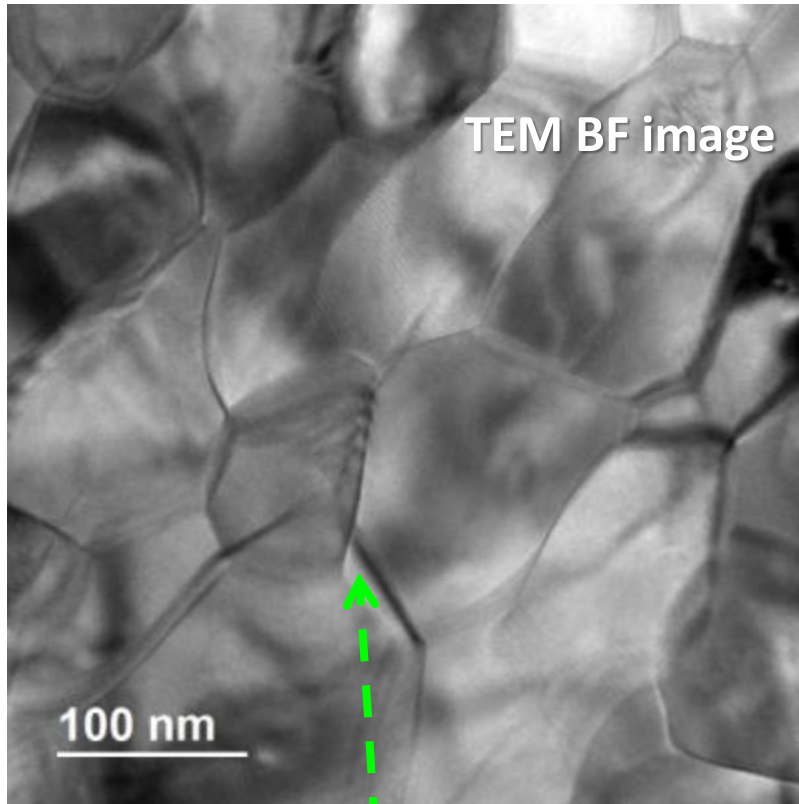


JEOL ARM BF(Bright Field) TEM Image

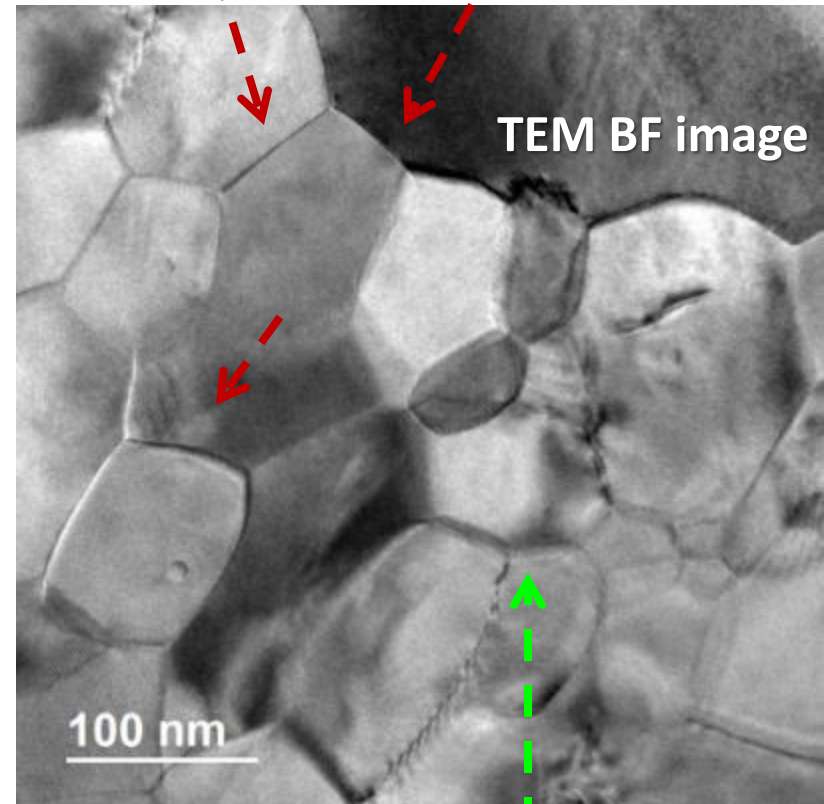


Cleaner and thin TEM foils are required for accurate analytical microscopy

Very clean TEM lamella produced by Low-Voltage FIB milling.



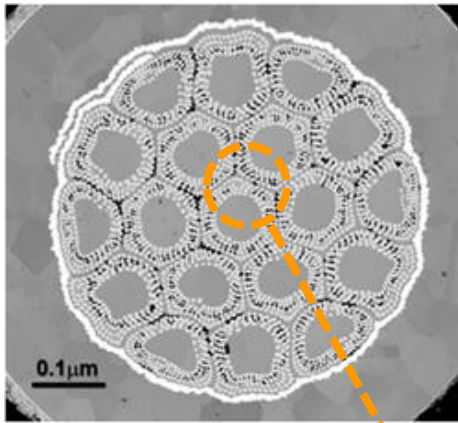
GB plane \parallel to electron beam:
higher spectrum signal



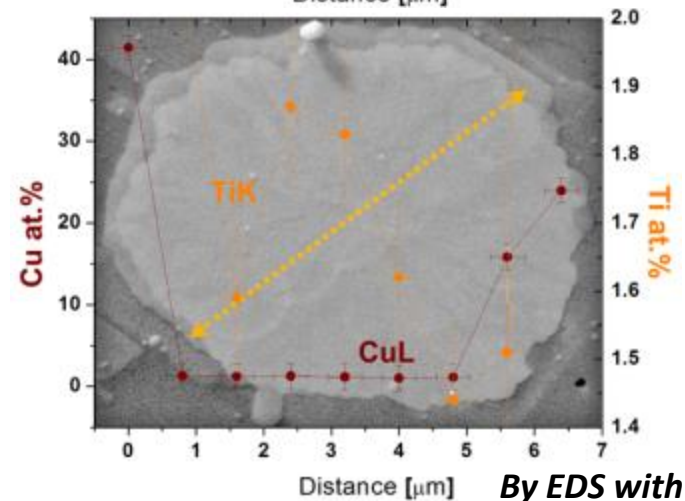
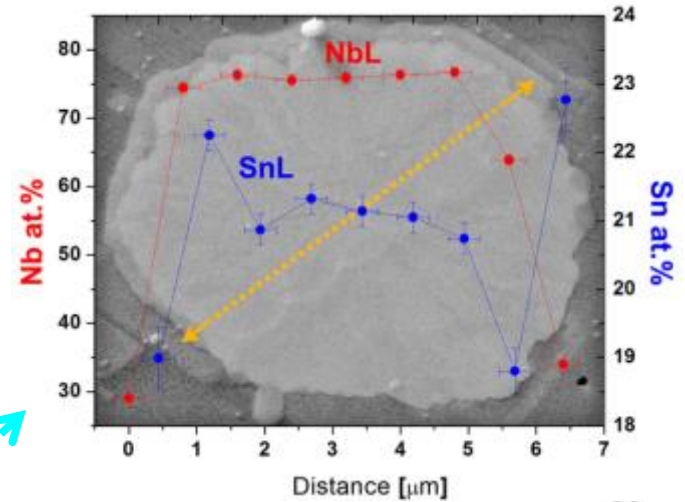
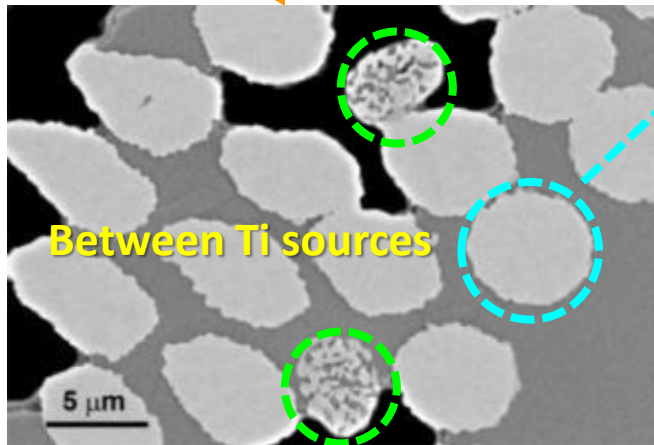
Highly tilted GB structure: hard to detect composition signal



A15 compositions in Ti-doped ITER strand: $\text{Sn} \approx 22\text{-}23\text{at}\%$, $\text{Ti}+\text{Sn} \approx 23.5\text{-}24.5\text{at}\%$



12 distributed Ti sources (Nb-47wt% Ti) in the sub element

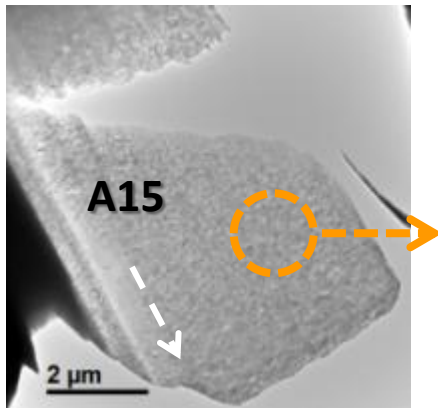


By EDS with FE-SEM

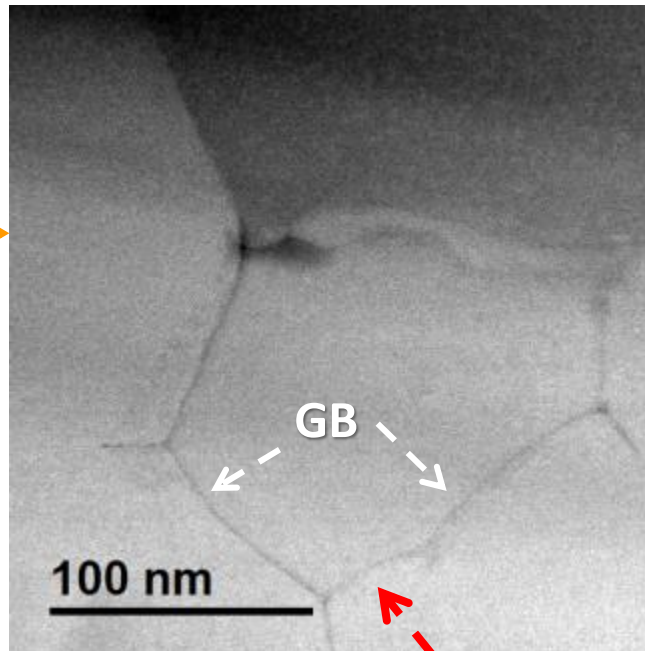


Successfully thinned grain boundary structure

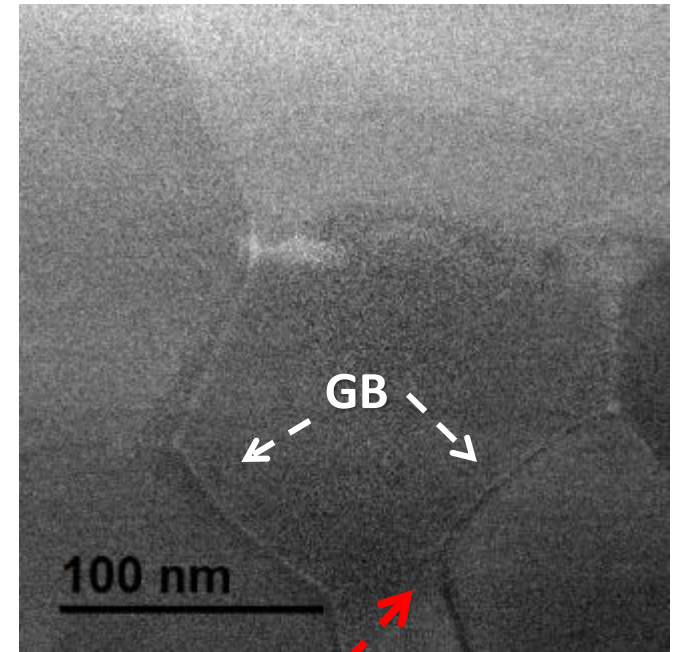
TEM BF Image



STEM ADF image: z-contrast



STEM BF image



Sample type A: Nb-47wt%Ti rod, 650°C/200hrs

GB contrast shows GB segregation



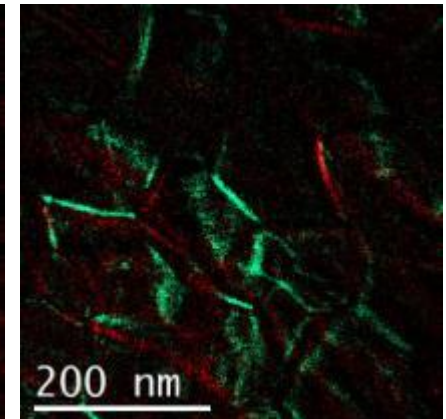
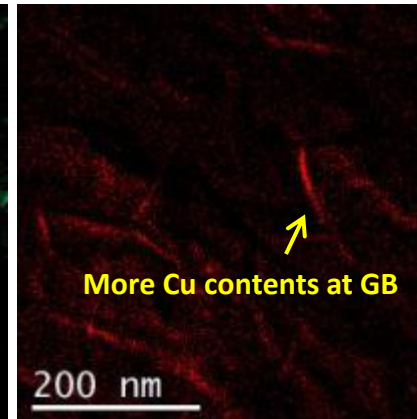
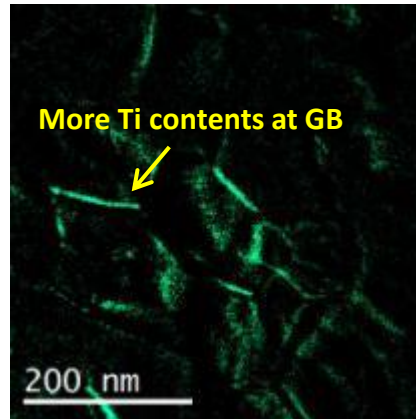
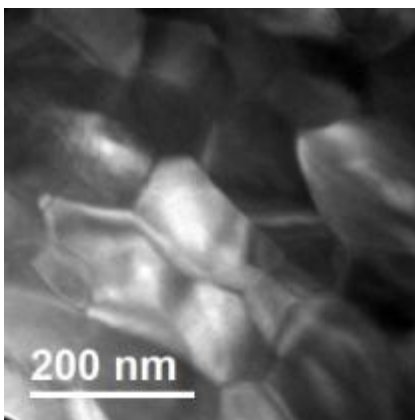
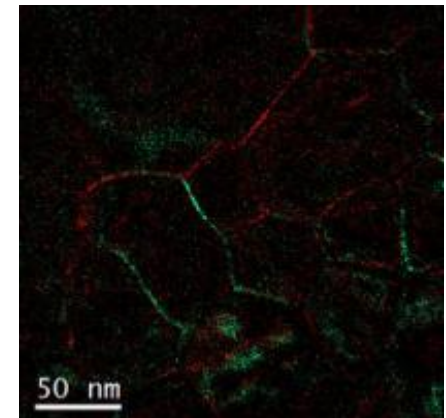
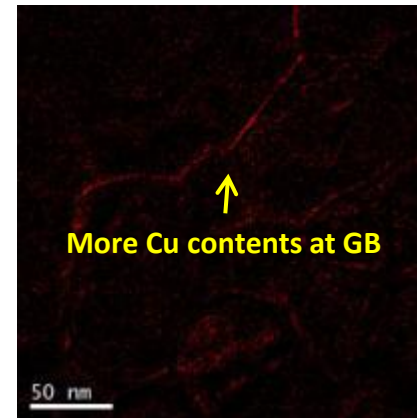
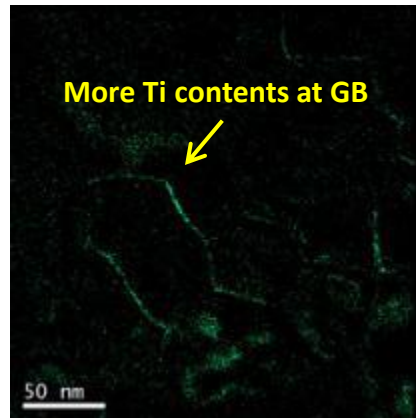
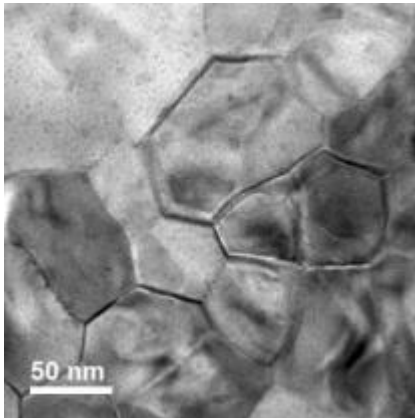
Ti-doped ITER Strand: EFTEM shows extensive Ti, Cu, or Ti & Cu segregation at GBs of Nb₃Sn

Zero-loss image

Ti: 450-460 eV

Cu: 920-930 eV

Ti + Cu



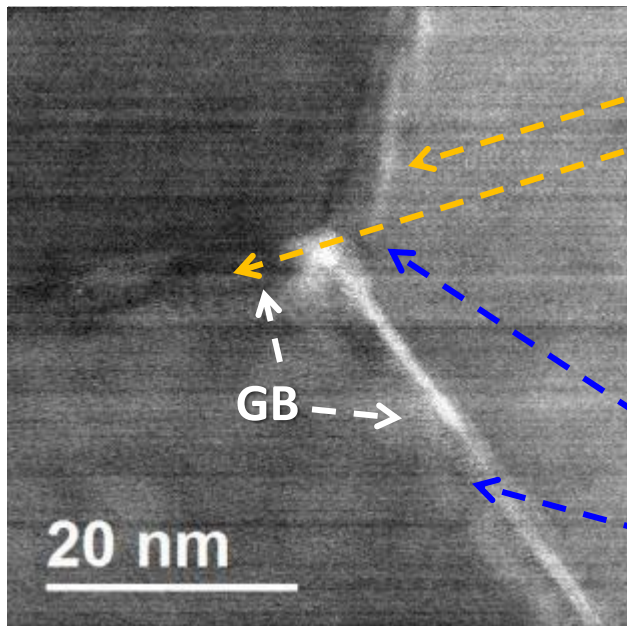
Sample type A: Nb-47wt%Ti rod, 650°C/200hrs



Ti-doped ITER Strand: GB segregation of Ti or Cu can also be observed by STEM-EELS

Sample type A: Nb-47wt%Ti rod, 650°C/200hrs

STEM AD image

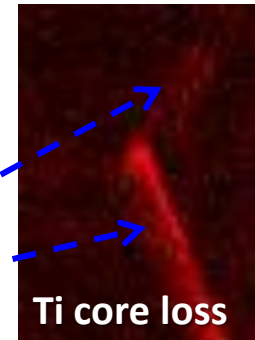
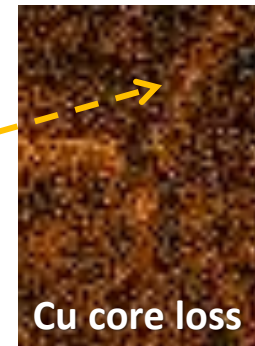


Bright contrast at GB: Cu segregation

Bright contrast: Ti segregation

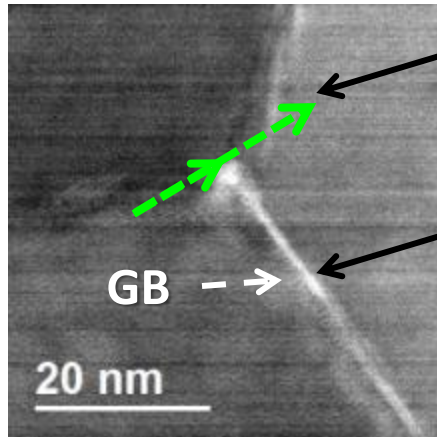
EELS spectrum

Color map Intensity



STEM-EDS also confirms Ti or Cu segregation at A15 GBs

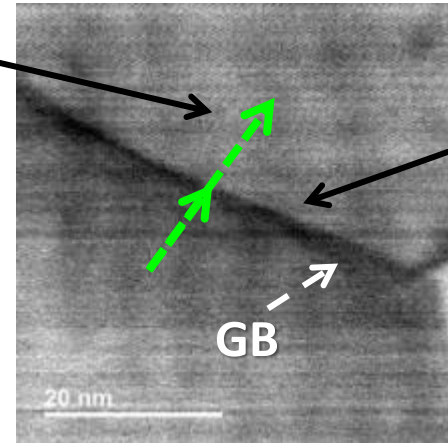
STEM BF image: EDS



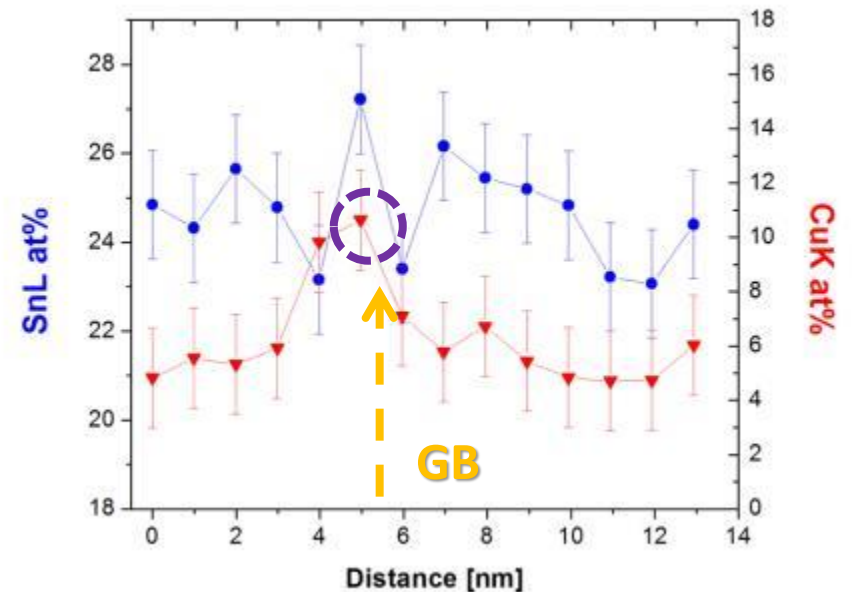
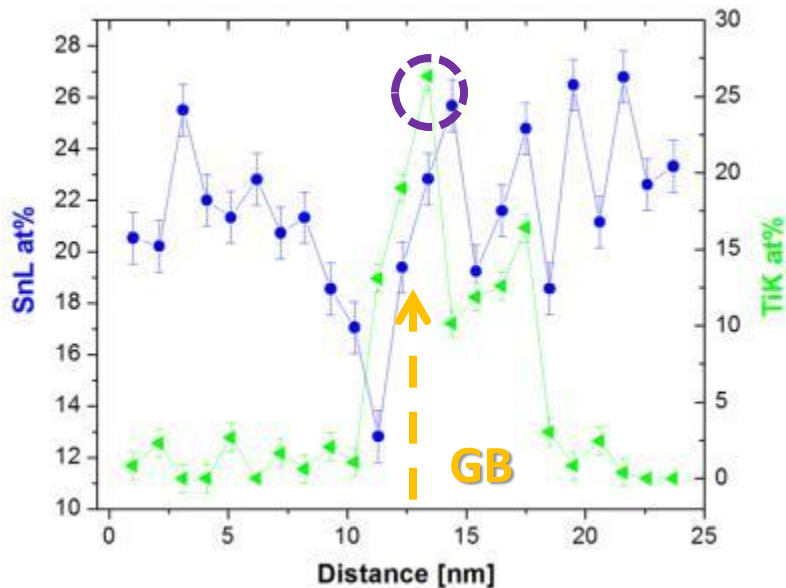
EDS Line scanning

Bright contrast: Ti content at GB

STEM BF image: EDS



Dark contrast: Cu content at GB



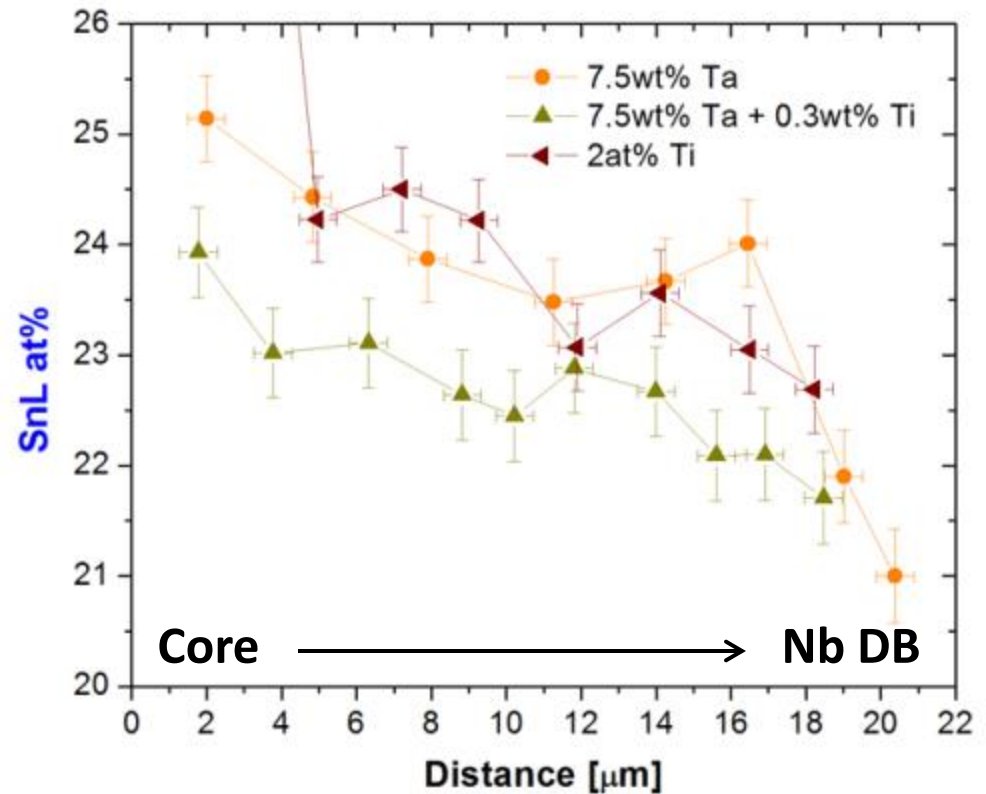
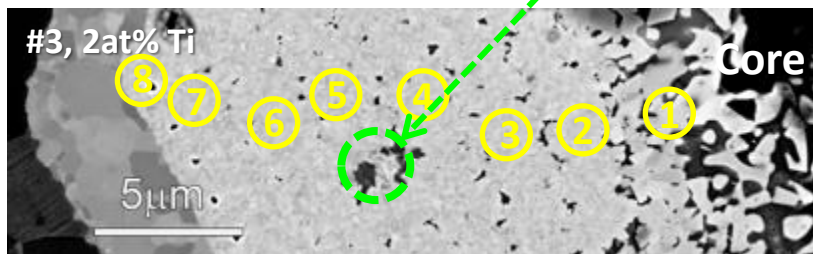
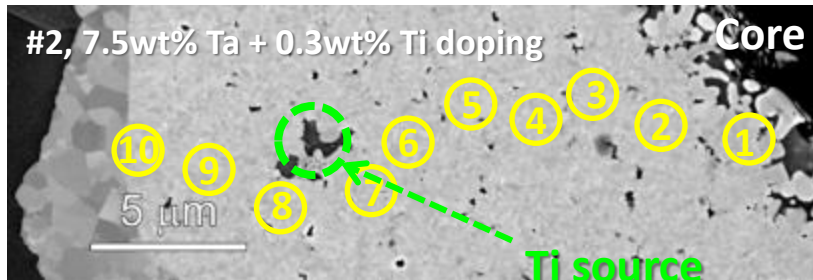
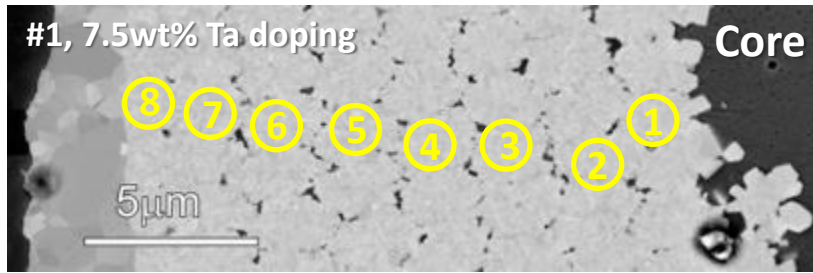
Significant variation is seen in superconducting properties between the 3 RRP[®] strand types

Doping type	$T_{c,Onset}$ [K]	$T_{c,peak}$ [K]	ΔT_c , K FWHM of $f(T_c)$ peak	ΔT_c , K 10-90% of $1-F(T_{c,Nb})$	$f(T_{c,peak})$	% Nb	RRR *	Volume superfluid at 16T, 2K	H_k^* Tesla	$J_c(12T)^*$ A/mm ²	$F_{p,max}^*$ GN/m ³
7.5wt% Ta	~18.4	17.37	1.50	3.51	0.40	8.7-10	251	38%	22.66	2712	57.6
7.5wt% Ta + 0.3wt% Ti	17.9	16.68	1.87	3.14	0.43	6.8-8.3	432	45%	24.75	2622	49.1
2a% Ti	18.1	17.25	1.42	2.83	0.50	8.1-8.9	369	38%	23.75	2872	56.7

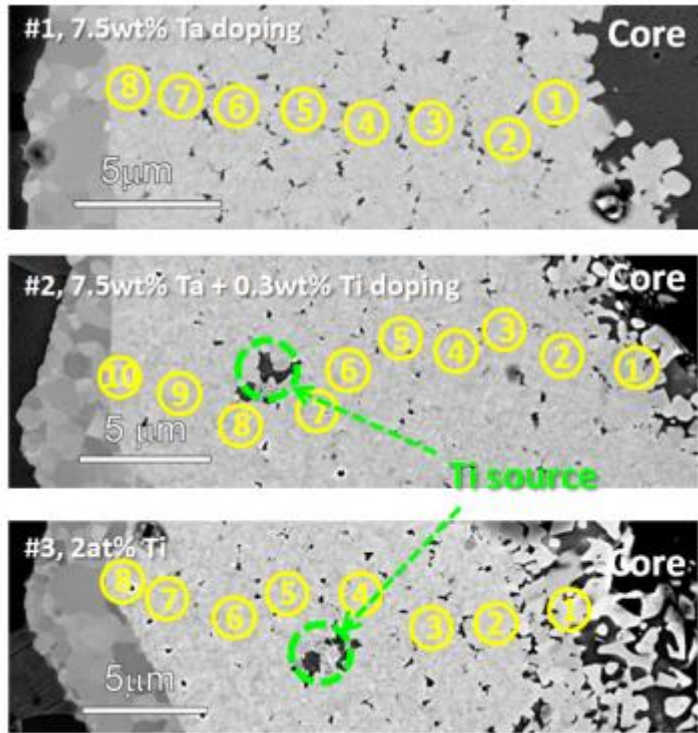
Measurement by Dr. C Tarantini

- **Ti** doping show the highest J_c and pinning force, but **Ta** show the highest T_c .
- **Ta + Ti** co-doping shows the lowest T_c , but it has a larger superconducting volume fraction and H_k .

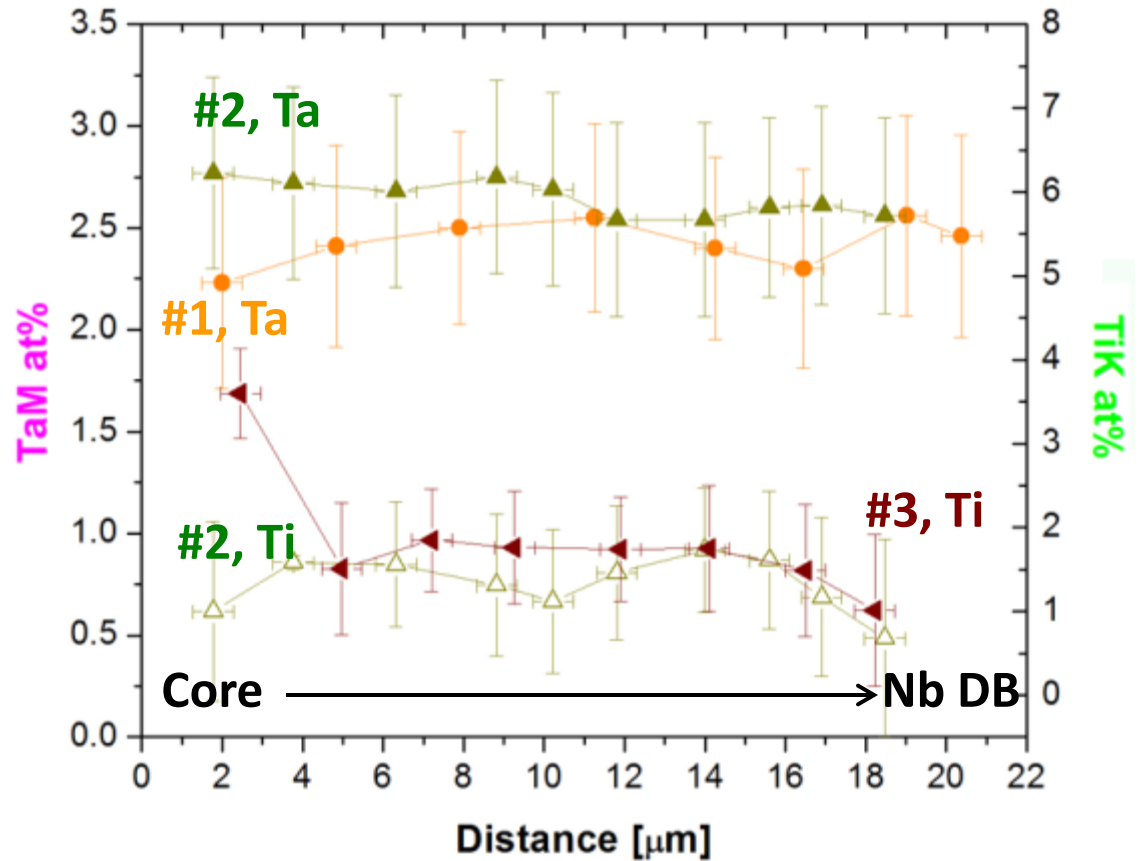
Ta + Ti co-doped strand has lower Sn content and greater gradient while Ta-doped strand is closer to A15 stoichiometry



Ta + Ti co-doping method seems to oversaturate Ta in A15 phase compared to single doping method



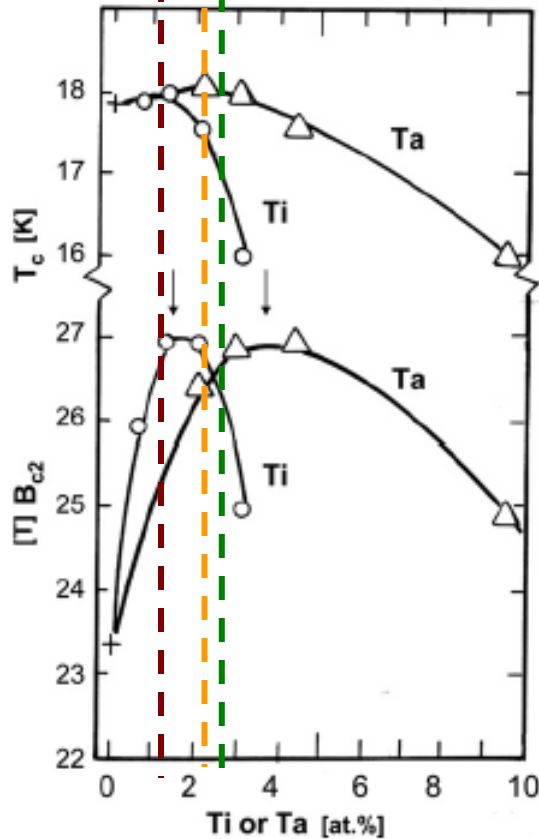
- #1, Ta at% for 7.5wt% Ta wire
- ▲— #2, Ta at% for 7.5wt% Ta + 0.3wt% Ti wire
- △— #2, Ti at% for 7.5wt% Ta + 0.3wt% Ti wire
- ◄— #3, Ti at% for 2at% Ti wire



#3, Sn \approx 23.77 at%,
Ti \approx 1.59 at%,
 $T_{c, \text{onset}} = 18.1$ K,
 $H_k = 23.75$ T

#1, Sn \approx 24.1 at%, Ta \approx 2.43 at%
 $T_{c, \text{onset}} = 18.4$ K, $H_k = 22.66$ T

#2, Sn \approx 22.77 at%, Ta \approx 2.65 at%,
Ti \approx 1.39 at% $T_{c, \text{onset}} = 17.9$ K, $H_k = 24.75$ T



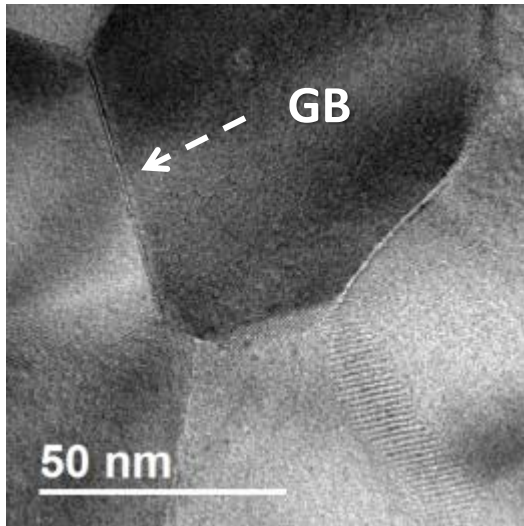
μ -scale composition analysis
with FESEM + EDS could
explain T_c properties of these
three differently doped
strands, but variation in J_c ,
 H_{c2} , and $\epsilon_{\text{irr},0}$ should be
addressed by atomic scale
analytical microscopy

M. Suenaga, et al, JAP 59, 840, (1986)

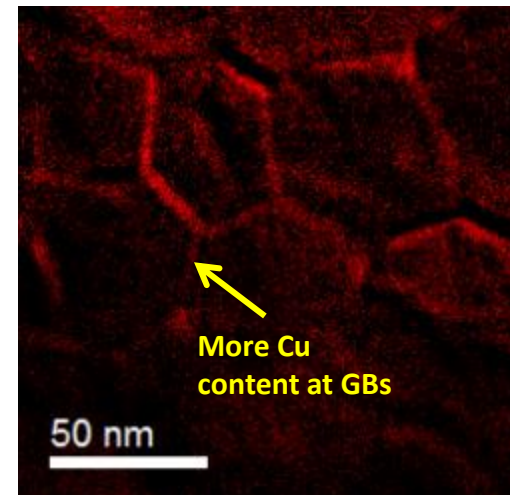
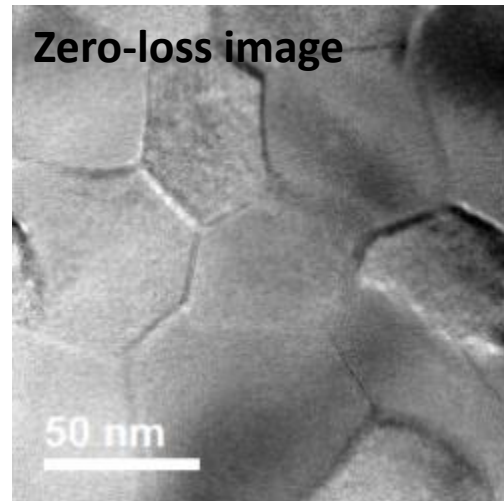
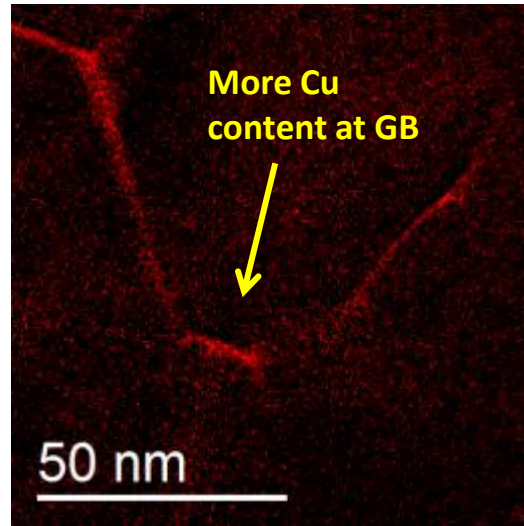


Ta-doped RRP Strand: EFTEM shows only Cu segregations at GBs of Nb₃Sn

Zero-loss image



Cu: 920-930 eV

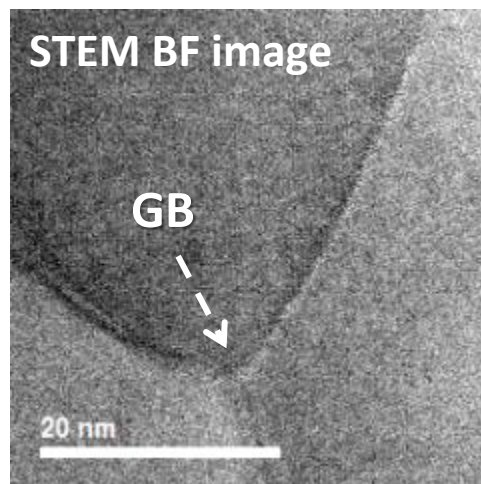
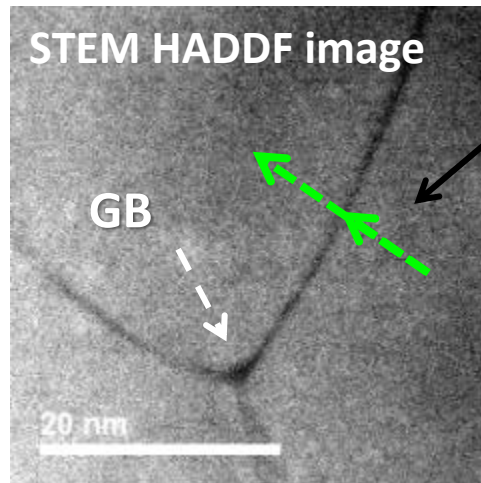


Sample type B, #1: 7.5wt% Ta, 640°C/48hrs

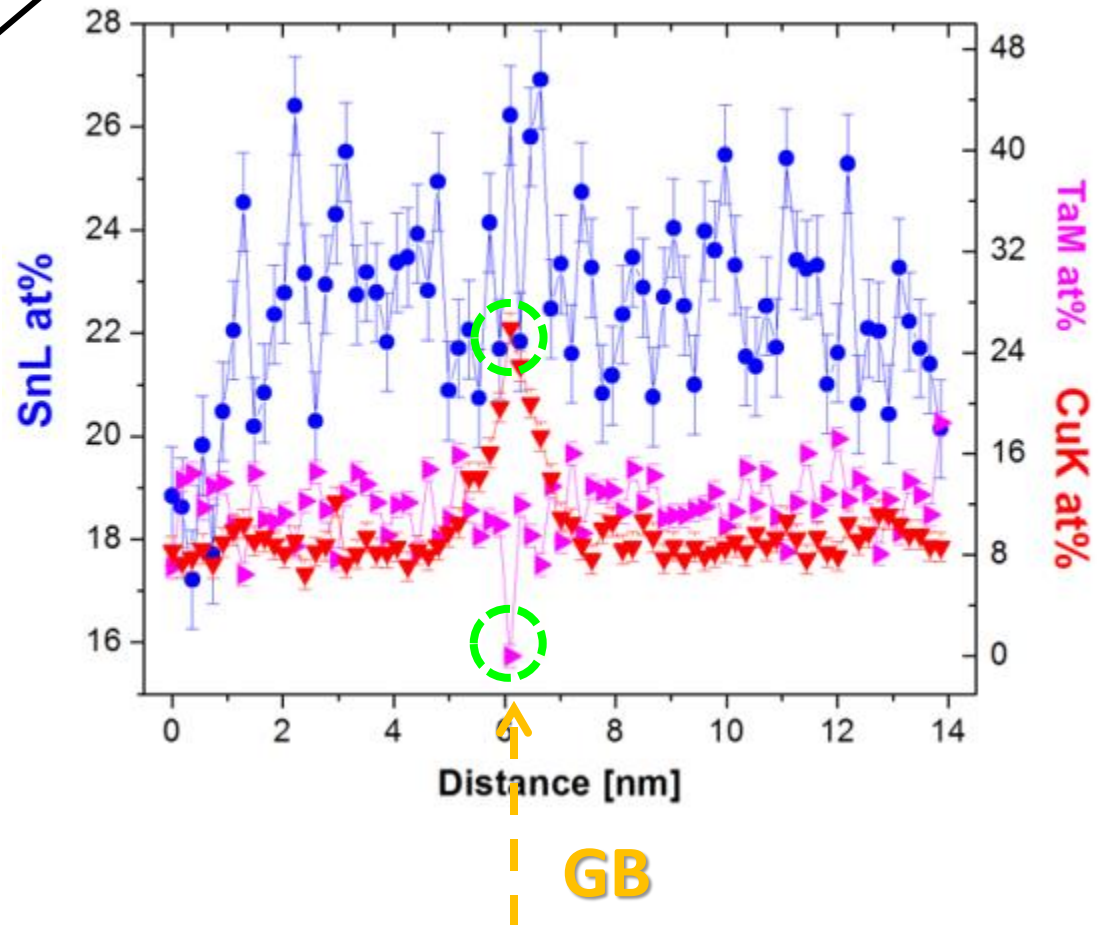
No observable Ta GB segregation



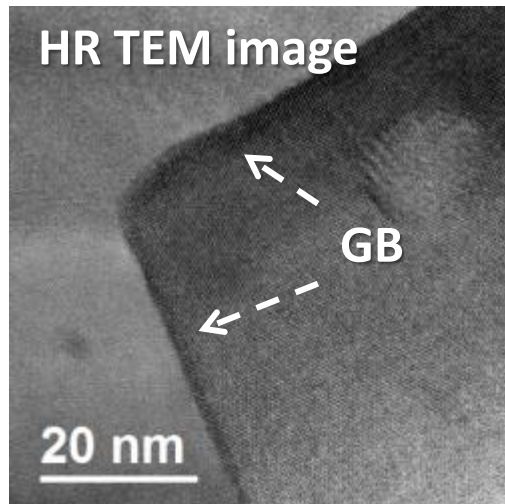
Ta-doped RRP[®] Strand: STEM-EDS shows GB Cu segregation but no "Ta" segregation



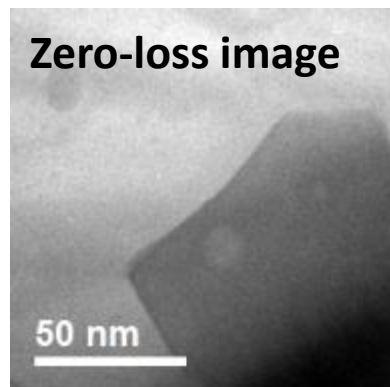
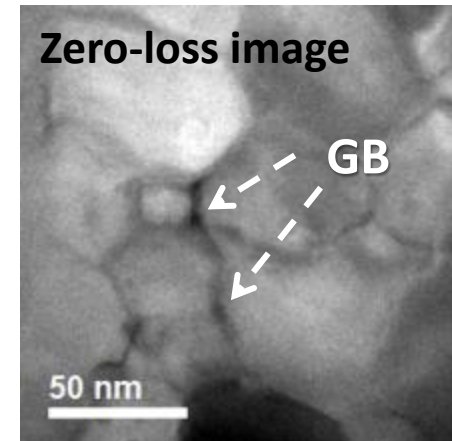
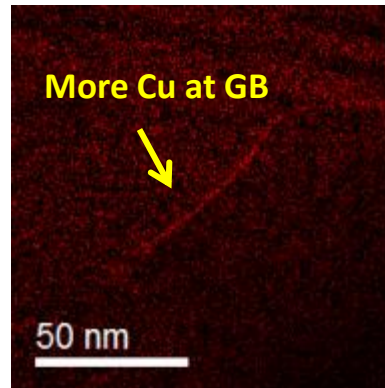
EDS Line scanning



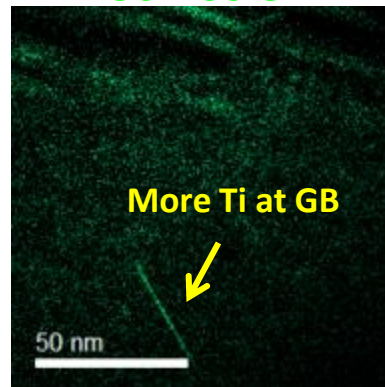
Ti-doped RRP[®] Strand: EFTEM shows extensive Ti and Cu segregation at A15 GBs



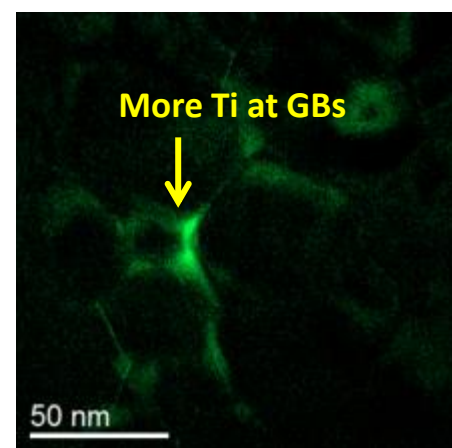
Cu: 920-930 eV



Ti: 450-460 eV



Ti: 450-460 eV

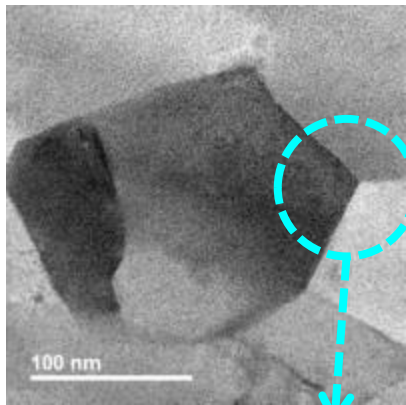


Sample type B, #3: 2at% Ti, 640°C/48hrs

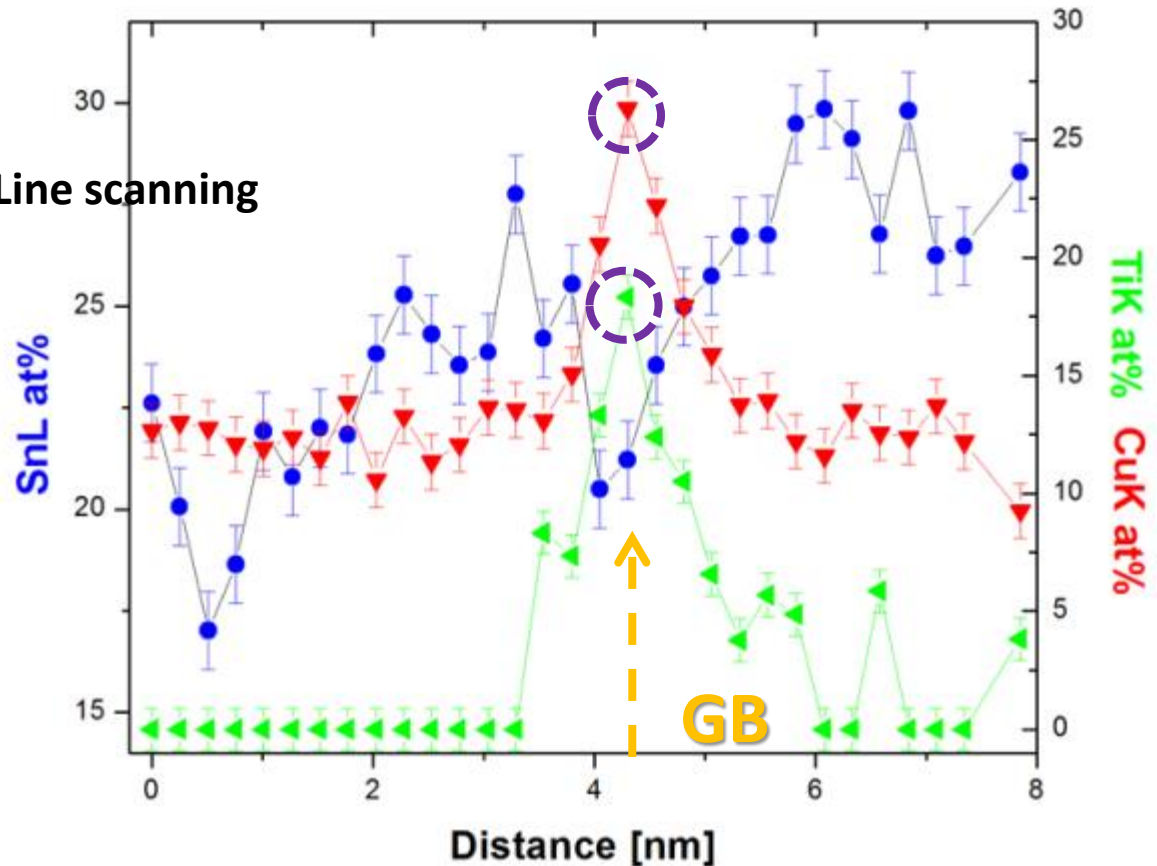
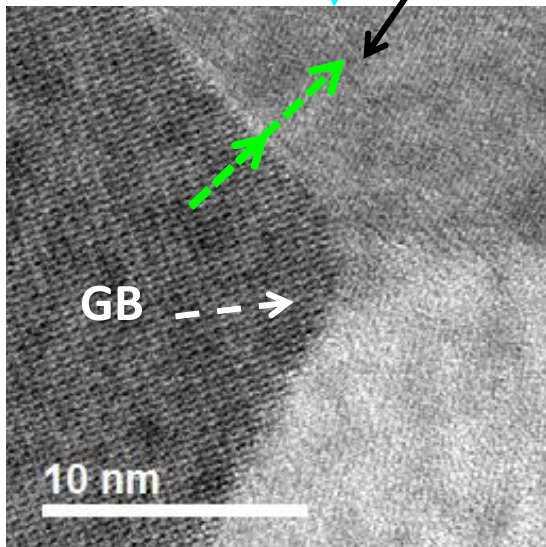


Ti-doped RRP[®] Strand: STEM-EDS shows Ti and Cu segregation at A15 GBs

STEM BF image

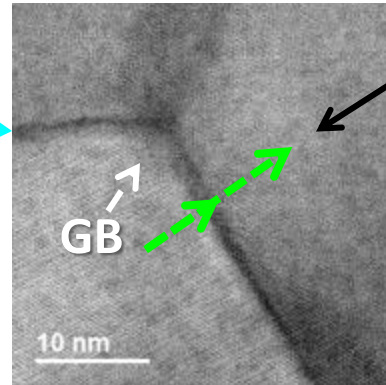
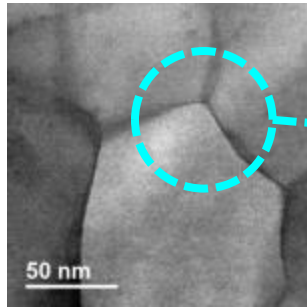


EDS Line scanning



Nb is poor at A15 GB, but Sn does not change across GB

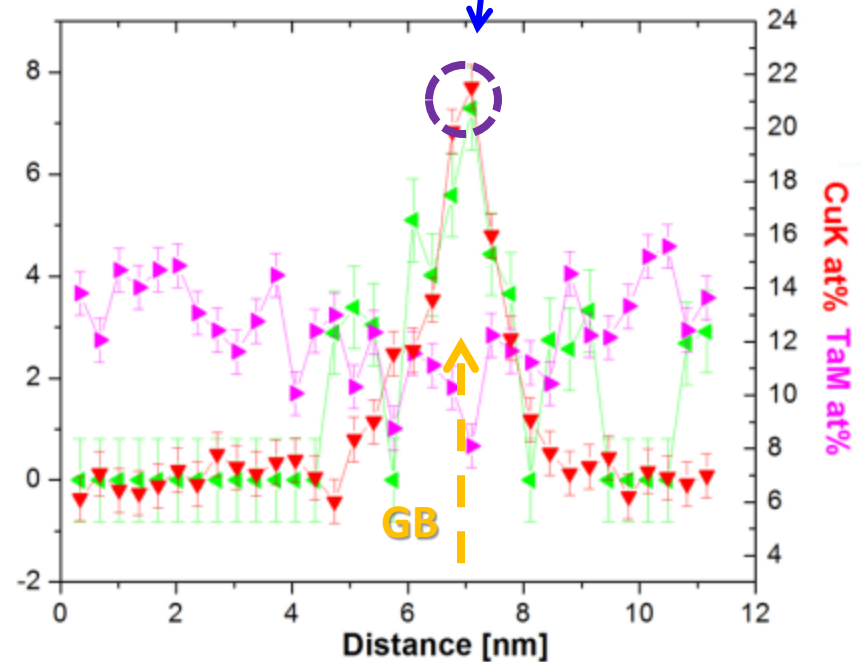
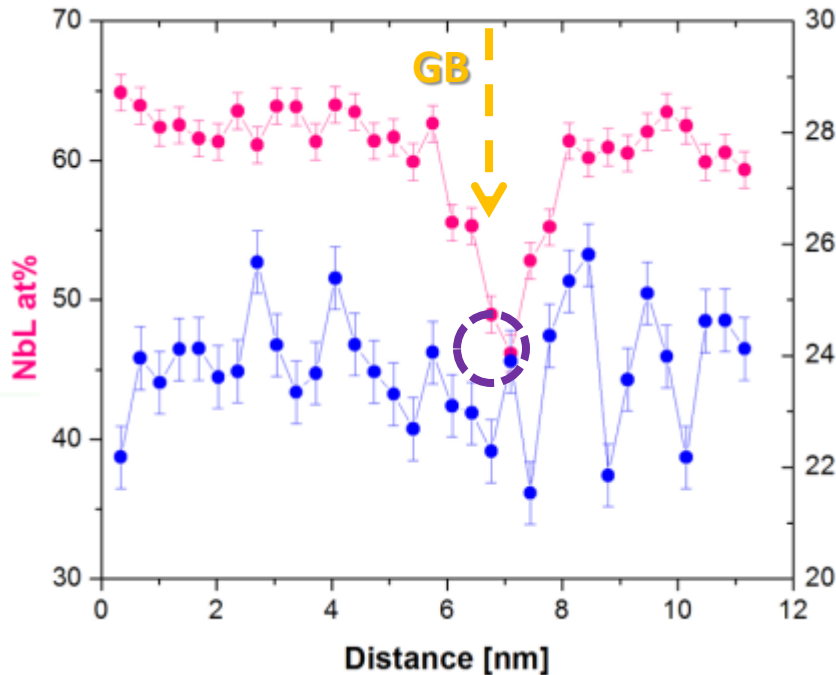
STEM BF image



EDS Line scanning

Ti and Cu segregation at the GB

*Ta + Ti doped RRP® strand:
7.5wt% Ta + 0.3wt% Ti*



Summary

Strand Type	Doping method	$\epsilon_{irr,0}$ (%) Avg. 0.1 mV/cm	$J_c(12T)^*$ A/mm ²	Compositions in A15 (at%) (Avg)			GB segregation
				Sn	Ti	Ta	
ITER	Nb-Ti rod	0.21	-	22.05	1.70		Ti, Cu
RRP (54/61)	7.5wt% Ta	0.04	2712	24.1		2.43	Only Cu
RRP (54/61)	7.5wt% Ta + 0.3wt% Ti	0.06	2622	22.77	1.39	2.65	Ti, Cu
RRP (54/61)	2at% Ti	0.24	2872	23.77	1.59		Ti, Cu

Conclusion 1

- Solid A15 phase identification with FE-SEM+EDS can properly determine the effect of doping on SC properties of Nb_3Sn strand.
 - Optimized Ta doping can enhance T_c compared with Ti.
 - Ti doping may reduce Sn content in A15 phase; it may be due to Ti replacement on Sn site.
- However, GBs effect of alloyed- Nb_3Sn strand on wire properties should be accomplished with atomic resolution analytical microscopy.



Conclusion 2

- Grain boundaries are both the primary flux-pinning centers and locations of mechanical weakness in Nb₃Sn strands
 - We have known for many years (e.g. Suenaga Auger studies) that the global GB composition changes with doping.
 - But we do not know if there are the variations with position, heat treatment, and architecture.
- Recent Atom probe measurements (MJR Sandim SuST 2013) and in this study a new generation of high-resolution analytical TEM/STEM combined with new sample Prep techniques now make it possible to determine grain boundary compositions in a wide variety of materials.
 - We can now start to answer these crucial questions. In this study we find these new results:
 - Ti and Cu sometimes alternatively segregate at GBs in RRP[®] and ITER strand.
 - Ti GB segregation levels vary significantly from grain to grain in RRP[®] and ITER strand (Ti doped by distributed Nb-47T rods).
 - However, Ta does not deposit at the GBs of A15.

